Product Summary

BV_{SSS}	$R_{SS(ON)\ MAX}$	I_S T_A = +25°C
12V	5.9mΩ @ V_{GS} = 4.5V	16.6A
	9.0mΩ @ V_{GS} = 2.5V	12.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{SS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Battery Management
- Load Switch
- Battery Protection

Features

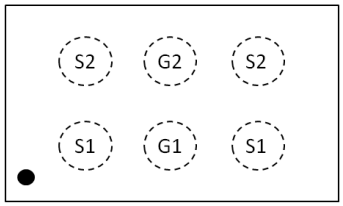
- CSP with Footprint 2.70mm × 1.81mm
- Height = 0.21mm for Low Profile
- ESD Protection of Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

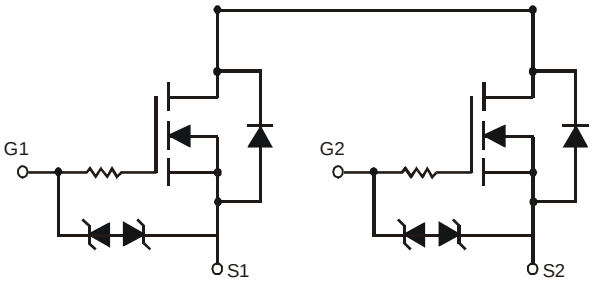
- Case: X3-DSN2718-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu. Solderable per MIL-STD-202, Method 208 e4

ESD PROTECTED

X3-DSN2718-6



Top View



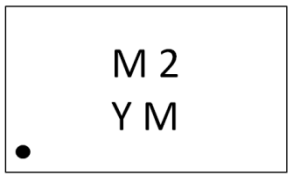
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1006UCA6-7	X3-DSN2718-6	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



M2 = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: F = 2018)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Source-Source Voltage			V_{SSS}	12	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Source Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_S	16.6 13.2	A
Continuous Source Current (Note 5) V_{GS} = 2.5V	Steady State	T_A = +25°C T_A = +70°C	I_S	12.1 9.7	A
Pulsed Source Current (Note 6)			I_{SM}	80	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P_D	1.0	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 7)	$R_{\theta JA}$	124.6	°C/W
Power Dissipation (Note 5)	P_D	2.4	W
Thermal Resistance, Junction to Ambient @T_A = +25°C (Note 5)	$R_{\theta JA}$	51.5	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Source-Source Breakdown Voltage	BV_{SSS}	12	-	-	V	V_{GS} = 0V, I_S = 1mA
Zero Gate Voltage Drain Current T_J = +25°C	I_{SSS}	-	-	1	µA	V_{SS} = 10V V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±10	µA	V_{GS} = ±8V, V_{SS}=0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	-	1.3	V	V_{SS} = 6V, I_S = 1mA
Static Source-Source On-Resistance	$R_{SS(ON)}$	3.5	5.0	5.9	mΩ	V_{GS} = 4.5V, I_S = 3A
		3.6	5.2	6.3		V_{GS} = 4.0V, I_S = 3A
		3.8	5.3	6.5		V_{GS} = 3.8V, I_S = 3A
		3.8	5.5	8.0		V_{GS} = 3.1V, I_S = 3A
		4.2	6.0	9.0		V_{GS} = 2.5V, I_S = 3A
Diode Forward Voltage	V_{SS}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 3A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	2,360	-	pF	V_{SS} = 6V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	666	-		
Reverse Transfer Capacitance	C_{rss}	-	325	-		
Total Gate Charge	Q_g	-	35.2	-	nC	V_{SS} = 6V, V_{GS} = 4.5V, I_S = 18A
Gate-Source Charge	Q_{gs}	-	7.0	-		
Gate-Drain Charge	Q_{gd}	-	8.3	-		
Gate Charge at V_{TH}	$Q_{g(TH)}$	-	4.2	-		
Turn-On Delay Time	$t_{D(ON)}$	-	615	-	ns	V_{SS} = 6V, V_{GS} = 4.5V, I_S = 3A
Turn-On Rise Time	t_R	-	1,447	-		
Turn-Off Delay Time	$t_{D(OFF)}$	-	2,736	-		
Turn-Off Fall Time	t_F	-	3812	-		

Notes:
5. Device mounted on FR-4 material with 1inch^2 (6.45cm^2), 2oz. (0.071mm thick) Cu.
6. Repetitive rating, pulse width limited by junction temperature.
7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

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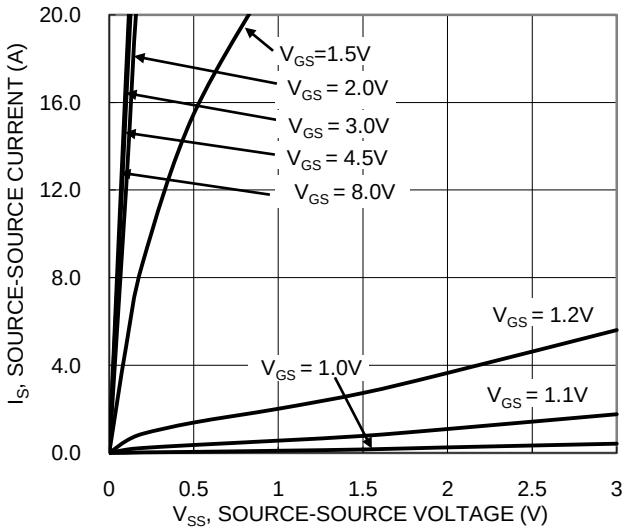

Figure 1. Typical Output Characteristic

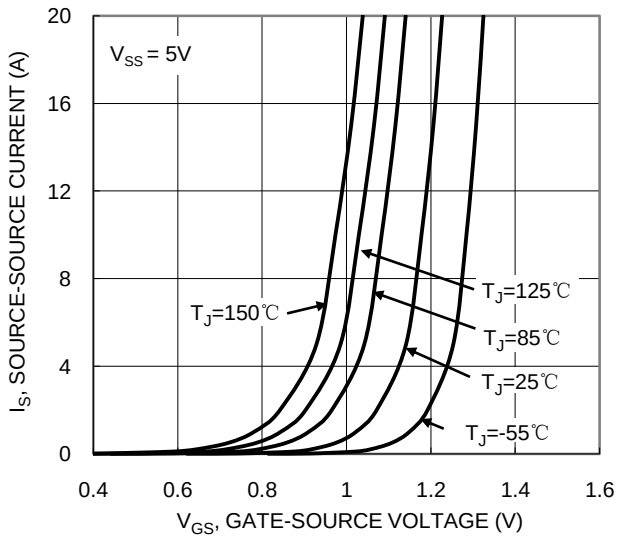

Figure 2. Typical Transfer Characteristic

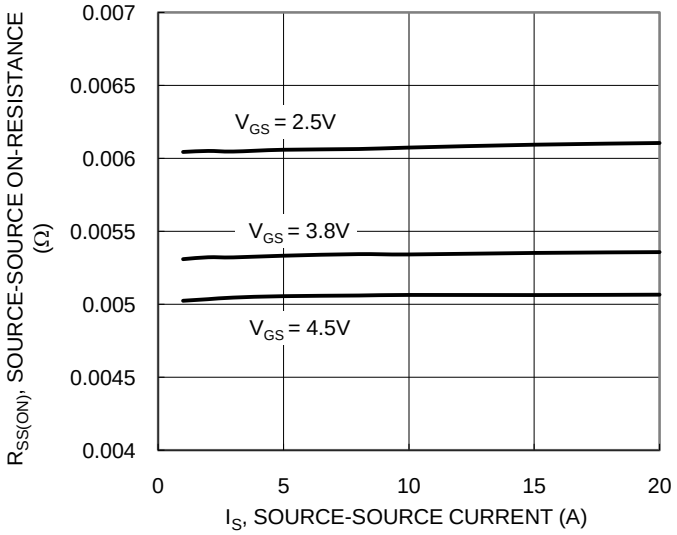

Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

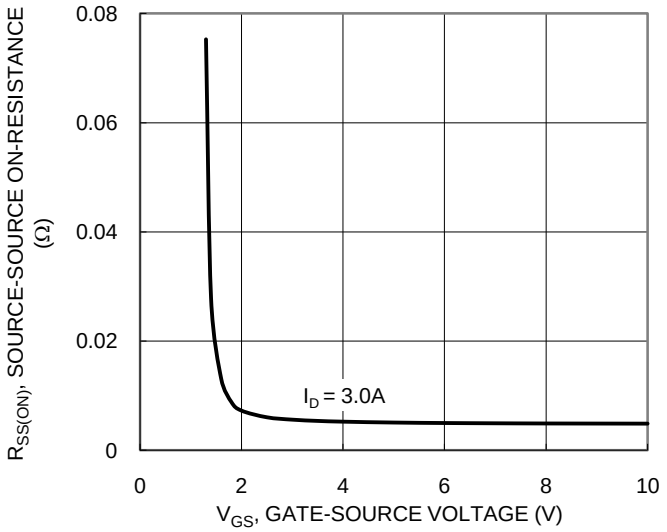

Figure 4. Typical Transfer Characteristic

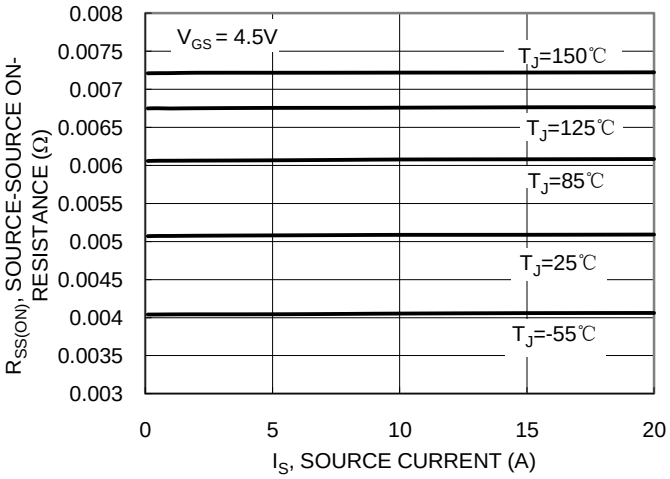

Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

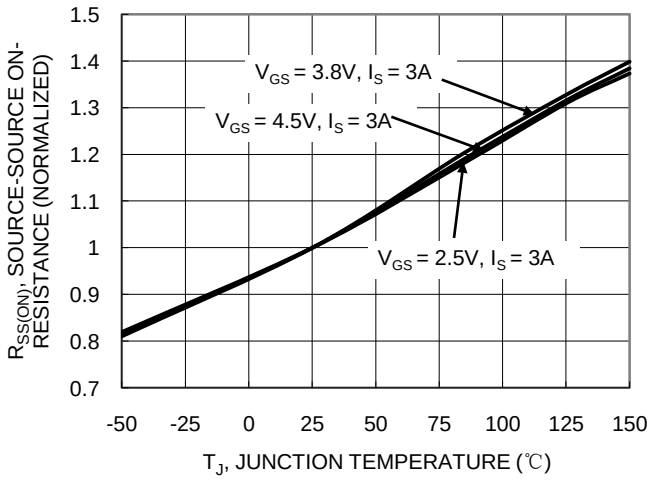

Figure 6. On-Resistance Variation with Junction Temperature

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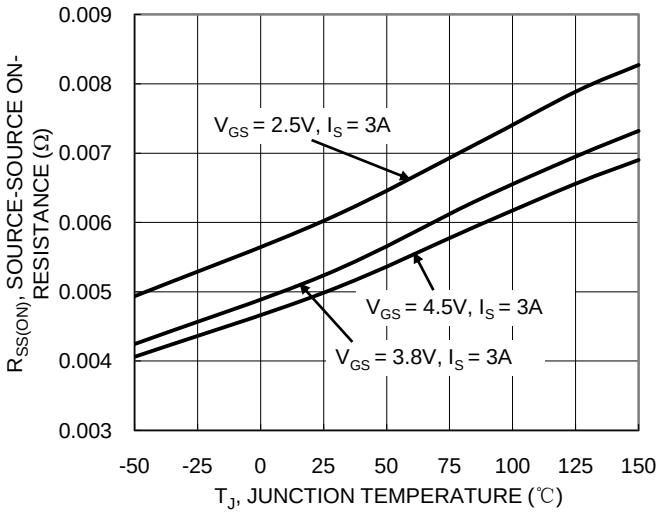

Figure 7. On-Resistance Variation with Junction Temperature

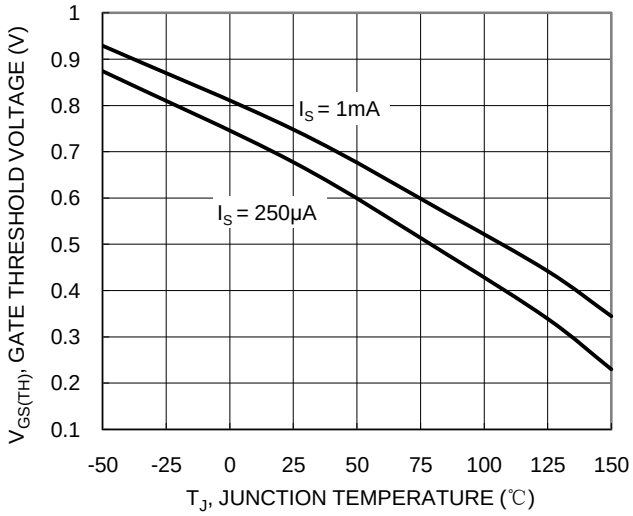

Figure 8. Gate Threshold Variation vs. Junction Temperature

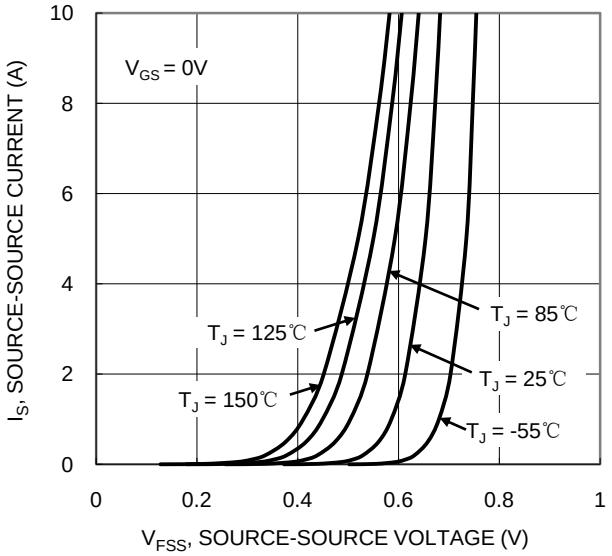

Figure 9. Diode Forward Voltage vs. Current

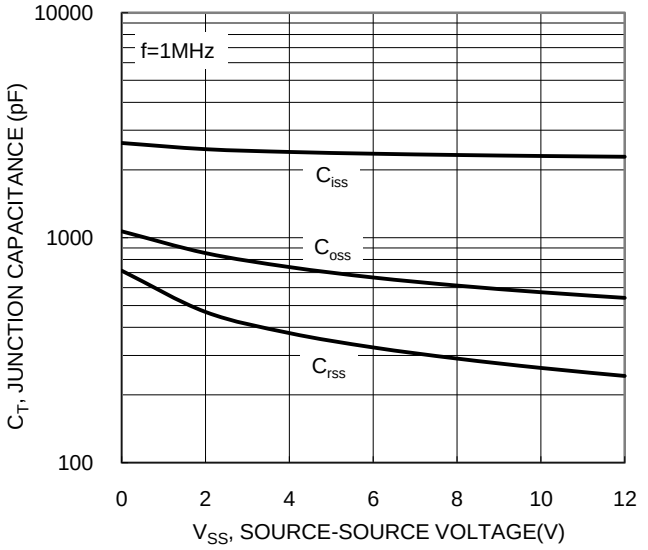

Figure 10. Typical Junction Capacitance

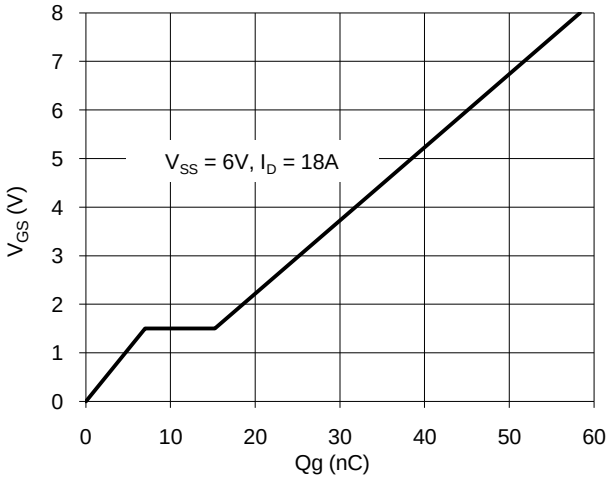

Figure 11. Gate Charge

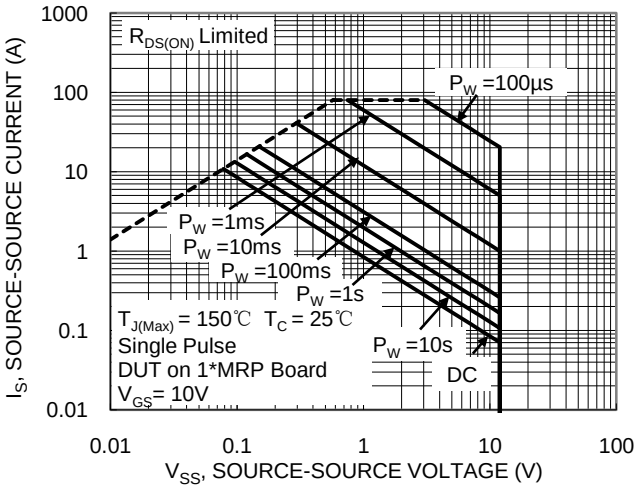

Figure 12. SOA, Safe Operation Area

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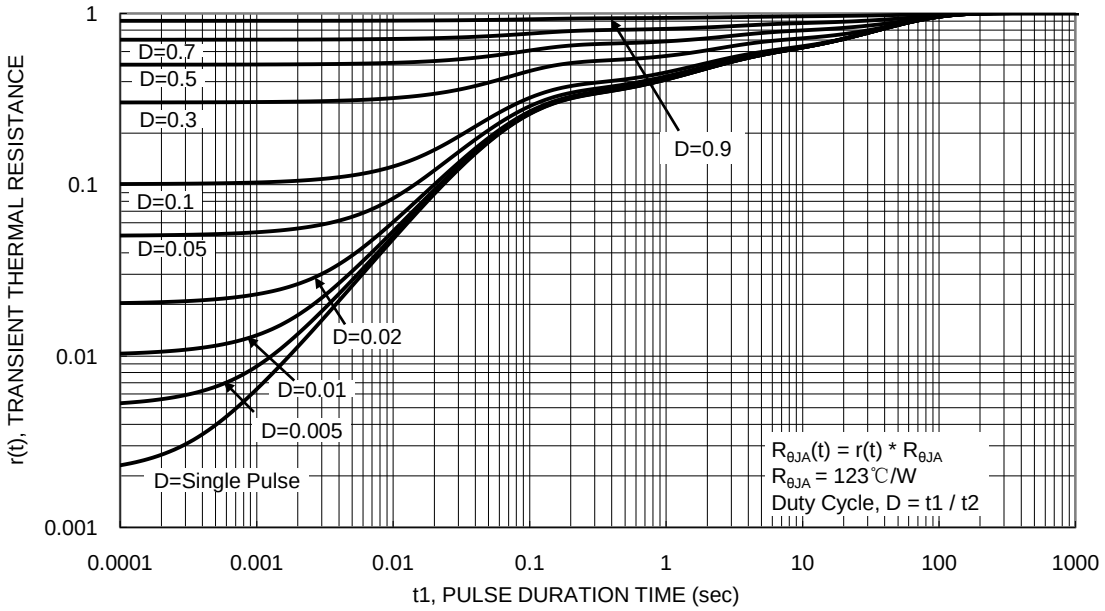

Figure 13. Transient Thermal Resistance

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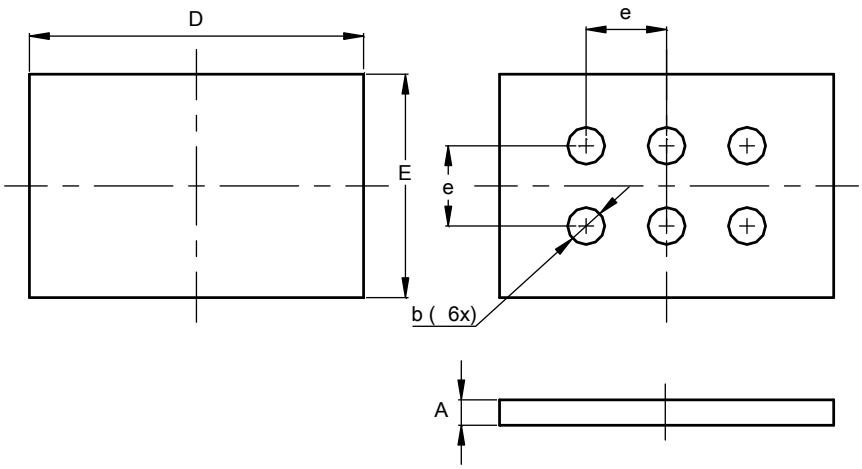
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X3-DSN2718-6

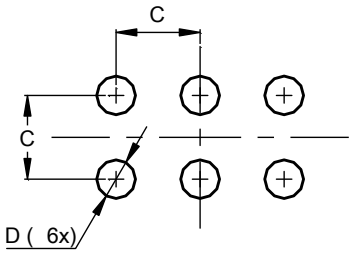


X3-DSN2718-6			
Dim	**Min**	**Max**	**Typ**
A	0.16	0.26	0.21
b	0.27	0.33	0.30
D	2.65	2.75	2.70
E	1.76	1.86	1.81
e	0.62	0.68	0.65
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X3-DSN2718-6



Dimensions	Value (in mm)
C	0.65
D	0.30

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